

CONFIRMATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Christophe MALEVILLE et al.

Confirmation No. 6754

Application No.: 10/809,918

Group Art Unit: 2812

Filing Date: March 26, 2004

Examiner: Beth E. Owens

For: METHOD FOR CHARACTERIZING A STEP
OF IMPLANTING IN A MATERIAL SUBSTRATE

Atty. Docket No.: 4717-13300

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, enclosed are copies of (8) references for the Examiner's review and consideration. These references was cited in the International Search Report and a copy is enclosed.

These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

No fee is believed to be due for the filing of this statement as it is being submitted prior to an initial office action for this application. Should any fees be required, however, please charge such fees to Winston & Strawn LLP Deposit Account No. 50-1814.

Respectfully submitted,

Date: _____

9/16/04



Allan A. Fanucci (Reg. No. 30,256)

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Enclosure

NY:888448.1

CONFIRMATION

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				ATTY. DOCKET NO.:		APPLICATION NO.:	
				4717-13300		10/809,918	
				APPLICANT:			
				C. Maleville et al.			
				FILING DATE:		GROUP:	
				March 26, 2004		2812	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	4 760 409	6/1998	Chen et al.	250	492.21	
	AB						
	AC						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
	AD	JP 61 043417 A English Abstract	3/1986	Japan	250		X
	AE	WO 99 08307 A	2/1999	PCT			X
	AF						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
	AG	Shiettekatte et al., XP004195210, "Dose and implantation temperature influence extended defects nucleation in c-Si", Nuclear instruments and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing Company, Vol. 164-165, pp. 425-430 (2000)					
	AH	L.J. Huang et al., XP000905645, "Model for blistering of hydrogen implanted silicon and its application to silicon-on-quartz", Electrochemical Society Proceedings, Processing of 8th International Symposium on Semiconductor Silicon Vol. 98-1, pp. 1373-1384 (1998)					
	AI	Da Silva et al., XP004242656, "The effects of implantation temperature on He bubble formation in silicon", Nuclear instrument and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing' Company, Amsterdam, NL, Vol. 175-177, pp. 335-339 (2001)					
	AJ	Bruel et al., XP000611125, "Application of Hydrogen Ion Beams To Silicon on Insulator Material Technology", Nuclear instrument and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing' Company, Amsterdam, NL, Vol. 108, No. 3, pp. 313-319 (1996)					
	AK	Lanzieri et al., XP000073904 "Activation Uniformity Improvement of Undoped semi-insulating Gaas with an improved Post-Implant Anneal Furnace", Journal of applied Physics, New York, Vol. 66, No. 8, pp 3643-3644 (1989)					
EXAMINER				DATE CONSIDERED			
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							